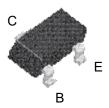


### FSB6726



SuperSOT™-3

# **PNP General Purpose Amplifier**

This device is designed for general purpose medium power amplifiers and switches requiring collector currents to 1.0 A. Sourced from Process 77.

## **Absolute Maximum Ratings\*** $T_{A=25^{\circ}\text{C unless otherwise noted}}$

Symbol	Parameter	FSB660/FSB660A	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	30	V
V <sub>CBO</sub>	Collector-Base Voltage	40	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
Ic	Collector Current - Continuous	1.5	Α
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

- 1) These ratings are based on a maximum junction temperature of 150°C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

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Symbol	Characteristic	Max	Units
		FSB6726	
P <sub>D</sub>	Total Device Dissipation	500	mW
R <sub>θ</sub> JA	Thermal Resistance, Junction to Ambient	250	°C/W

## **PNP General Purpose Amplifier**

(continued)

## **Electrical Characteristics**

T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10 mA	30		V
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 100 μA	40		V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 100 μA	5		V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 40 V		100	nA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V		100	nA
ON CHAR	ACTERISTICS*				
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 100 mA, V <sub>CE</sub> = 1 V	60		-
		$I_C = 1 A$ , $V_{CE} = 1V$	50	250	-
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1 A, I <sub>B</sub> = 100 mA		500	mV
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 1 A, V <sub>CE</sub> = 1 V		1.2	V
SMALL SI	IGNAL CHARACTERISTICS				
C <sub>cb</sub>	Collector-Base Capacitance	V <sub>CB</sub> = 10 V, f = 1MHz		30	pF
hfe	Small Signal Current Gain	I <sub>C</sub> = 50 mA,V <sub>CE</sub> = 10V, f=20MHz	2.5	25	-

\*Pulse Test: Pulse Width  $\leq 300~\mu\text{s},~\text{Duty Cycle} \leq 2.0\%$ 

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- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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### **Definition of Terms**

Datasheet Identification	Product Status	Definition
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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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